

BF397 is PNP silicon transistor designed for high voltage applications.

TO-92F



CBE

### ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	90V
Collector-Emitter Voltage	VCEO	90V
Emitter-Base Voltage	VEBO	6V
Total Power Dissipation	P <sub>tot</sub>	625mW
Collector Current	I <sub>C</sub>	100mA
Operating Junction & Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150°C

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	90		V	I <sub>C</sub> =10μA I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BVCEO	90		V	I <sub>C</sub> =10mA I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BVEBO	6		V	I <sub>E</sub> =10μA I <sub>C</sub> =0
Collector Cutoff Current	ICBO		50	nA	V <sub>CB</sub> =70V I <sub>E</sub> =0
Emitter Cutoff Current	IEBO		50	nA	V <sub>EB</sub> =4V I <sub>C</sub> =0
D.C. Current Gain	HFE	20			I <sub>C</sub> =100μA V <sub>CE</sub> =10V
		25			I <sub>C</sub> =1mA V <sub>CE</sub> =10V
		40	250		I <sub>C</sub> =10mA V <sub>CE</sub> =10V
		20			I <sub>C</sub> =100mA V <sub>CE</sub> =10V
Base-Emitter Saturation Voltage	V <sub>BE</sub> (sat)		0.9	V	I <sub>C</sub> =10mA I <sub>B</sub> =1mA
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)		0.5	V	I <sub>C</sub> =10mA I <sub>B</sub> =1mA



MICRO ELECTRONICS LTD. 美科有限公司

38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro Hx.  
P.O. Box 9477, Kwun Tong. Tel: 3-430181-6, 3-893363, 3-892423, 3-898224 FAX: 3-410321